

May 20, 2022

NT1192FAAE1S **Lower L-band GNSS LNA**

S-parameter, noise parameter simulation data (Standard Condition)

Ver.0

- S-parameter simulation data
- Max gain, NFmin simulation data
- Gain circle simulation data (Source/Load impedance)
- NF circle simulation data
- Simulation condition
- Simulation circuit
- s2p file

s2p file at $V_{DD}=2.8V$: NT1192FAAE1S_2r8v_v0.s2p

s2p file at $V_{DD}=1.8V$: NT1192FAAE1S_1r8v_v0.s2p

Written by Ryo Sekiguchi

Approved by Susumu Takagi

Nisshinbo Micro Devices Inc.

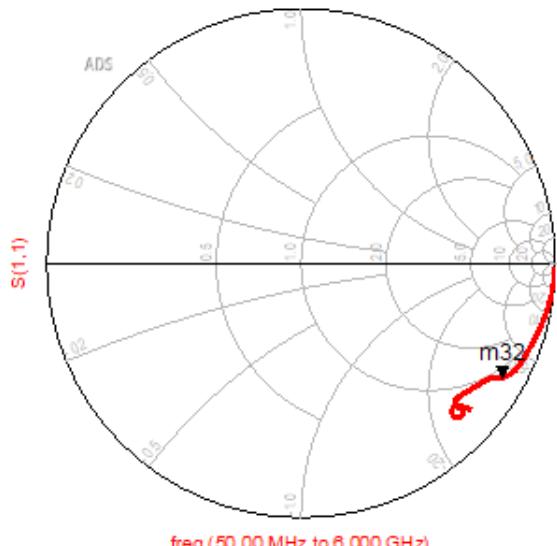
Electronic Devices Business Headquarters
Technology Development Division
RF Product Development Department
RFIC Design Section



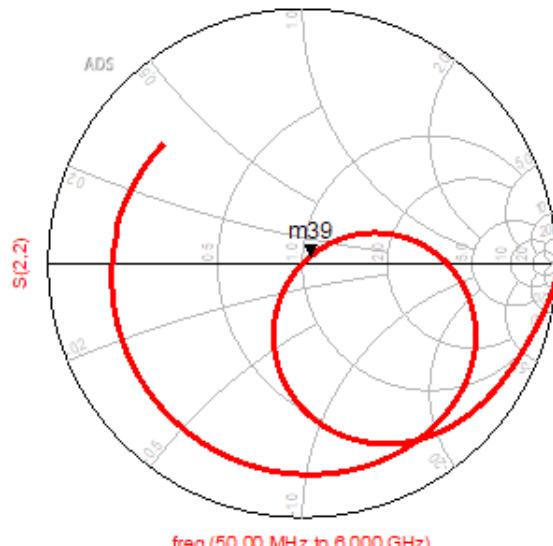
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■ S-parameter simulation data 1

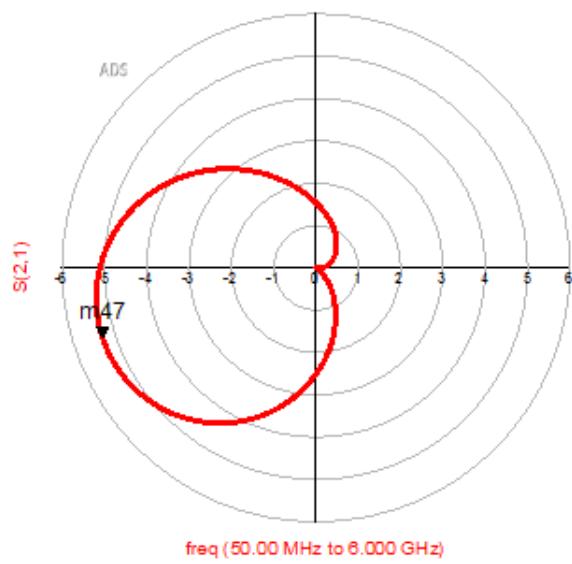
Condition: f=50MHz~6GHz, V_{DD}=2.8V, V_{CTL}=1.8V, Ta=+25°C, Z_s=Z_l=50ohm



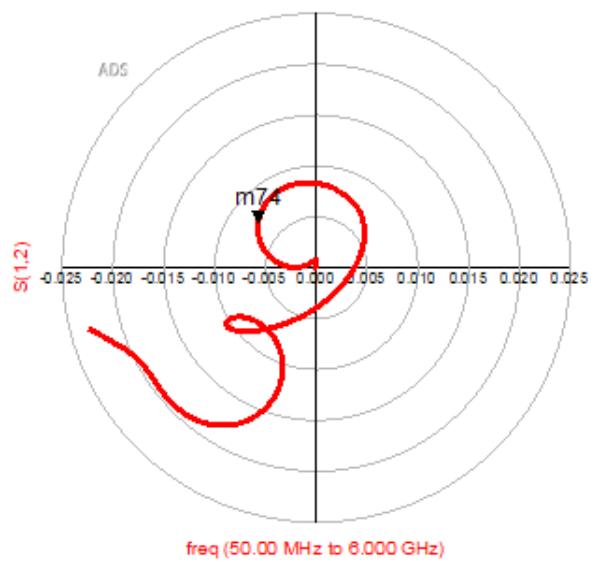
m32
freq=1.225 GHz
S(1,1)=0.911 / -29.515
impedance = $Z_0 \cdot (0.700 - j3.672)$

S11

m39
freq=1.225 GHz
S(2,2)=0.043 / 39.970
impedance = $Z_0 \cdot (1.087 + j0.050)$

S22

m47
freq=1.225 GHz
S(2,1)=5.297 / -161.896

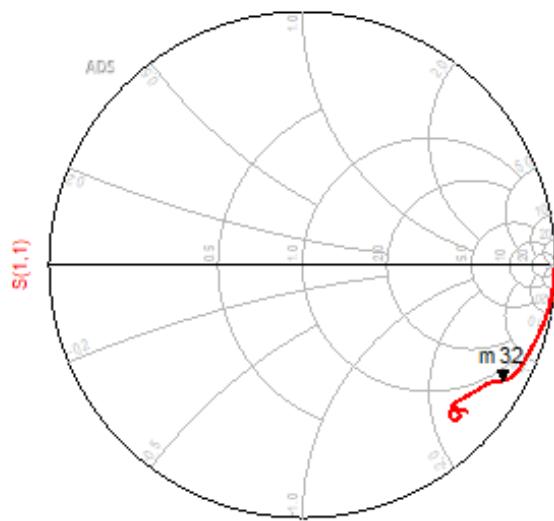
S21

m74
freq=1.225 GHz
S(1,2)=0.007 / 142.120

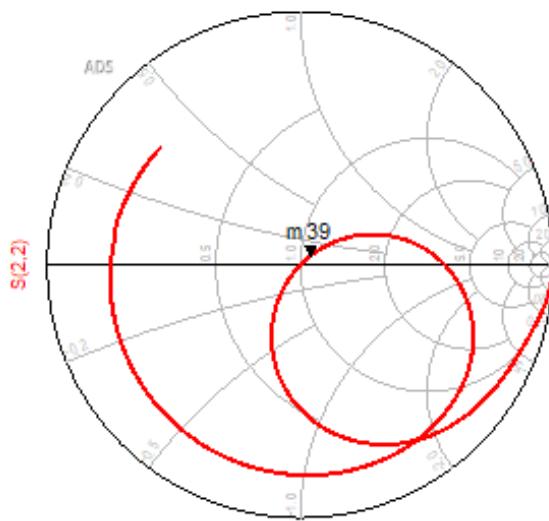
S12**Nissinbo Micro Devices Inc.**

■ S-parameter simulation data 2

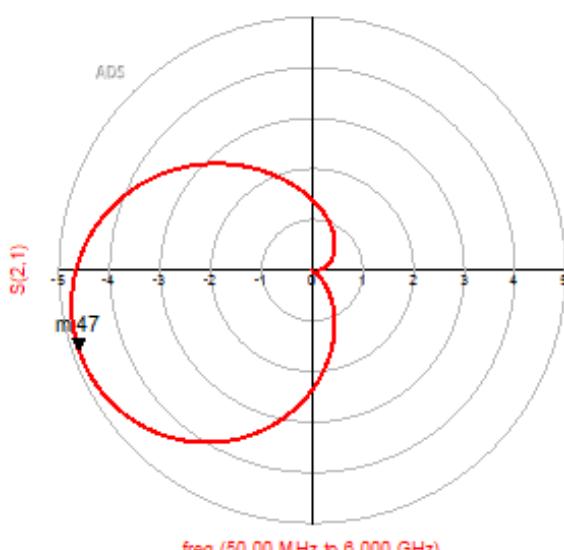
Condition: f=50MHz~6GHz, V_{DD}=1.8V, V_{CTL}=1.8V, Ta=+25°C, Z_s=Z_l=50ohm



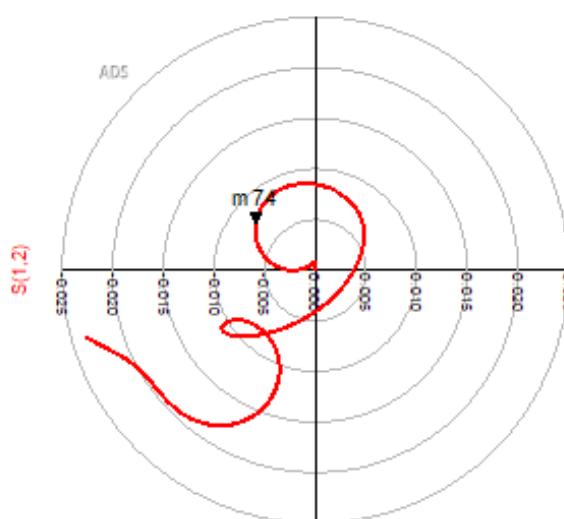
S(1,1)
freq (50.00 MHz to 6.000 GHz)
m32
freq=1.225 GHz
S(1,1)=0.915 / -30.042
impedance = $20^{\circ} \times (0.647 - j3.619)$

S11

S(2,2)
freq (50.00 MHz to 6.000 GHz)
m39
freq=1.225 GHz
S(2,2)=0.051 / 40.908
impedance = $20^{\circ} \times (1.078 + j0.073)$

S22

S(2,1)
freq (50.00 MHz to 6.000 GHz)
m47
freq=1.225 GHz
S(2,1)=4.869 / -161.114

S21

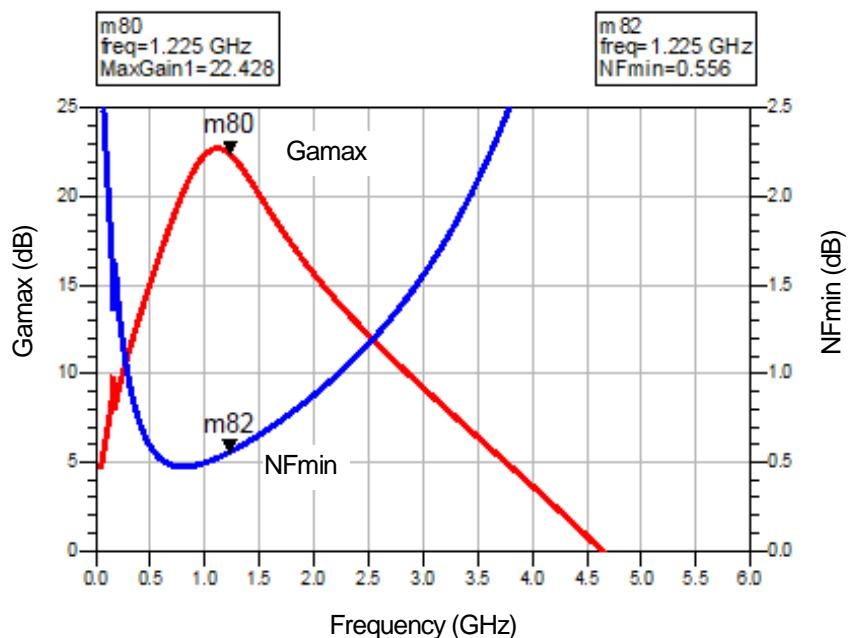
S(1,2)
freq (50.00 MHz to 6.000 GHz)
m74
freq=1.225 GHz
S(1,2)=0.007 / 141.703

S12

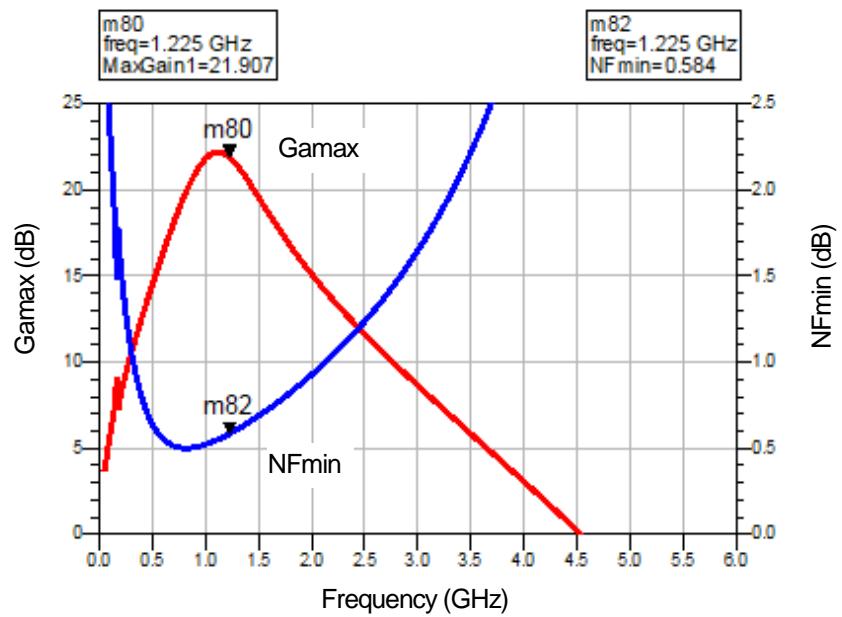
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■ Max gain, NFmin simulation data

Condition: f=50MHz~6GHz, V_{DD}=2.8V, V_{CTL}=1.8V, Ta=+25°C, Z_s=Z_l=50ohm

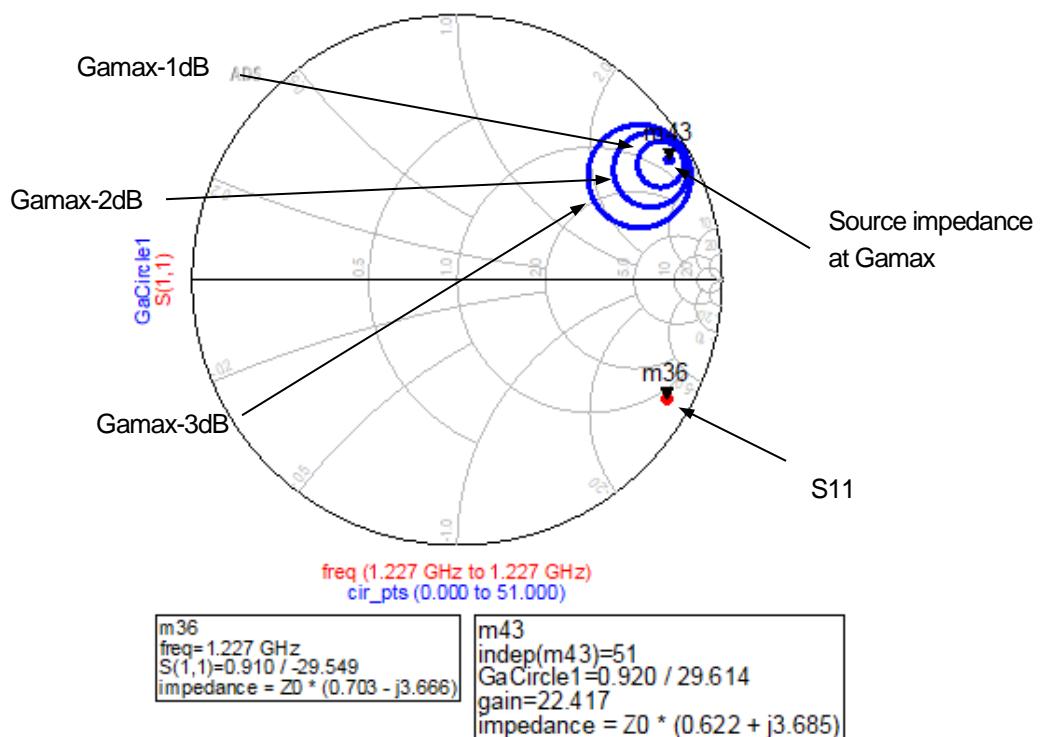


Condition: f=50MHz~6GHz, V_{DD}=1.8V, V_{CTL}=1.8V, Ta=+25°C, Z_s=Z_l=50ohm

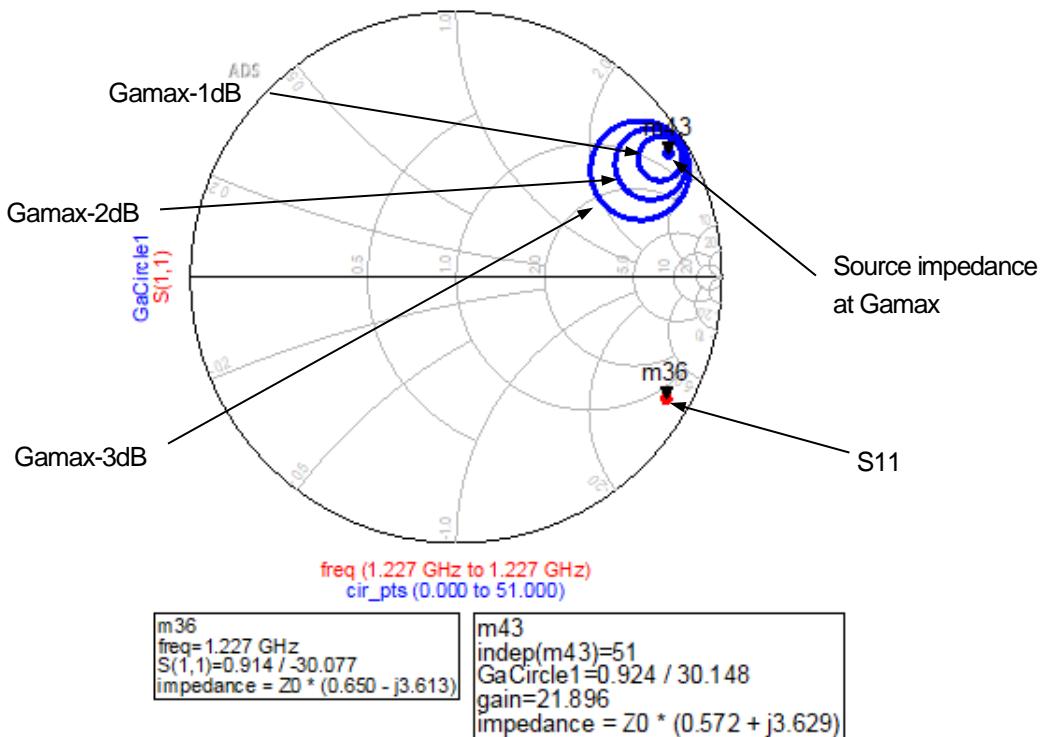


■ Gain circle simulation data (Source impedance)

Condition: f=1.227GHz, V_{DD}=2.8V, V_{CTL}=1.8V, Ta=+25°C, Z_s=Z_l=50ohm

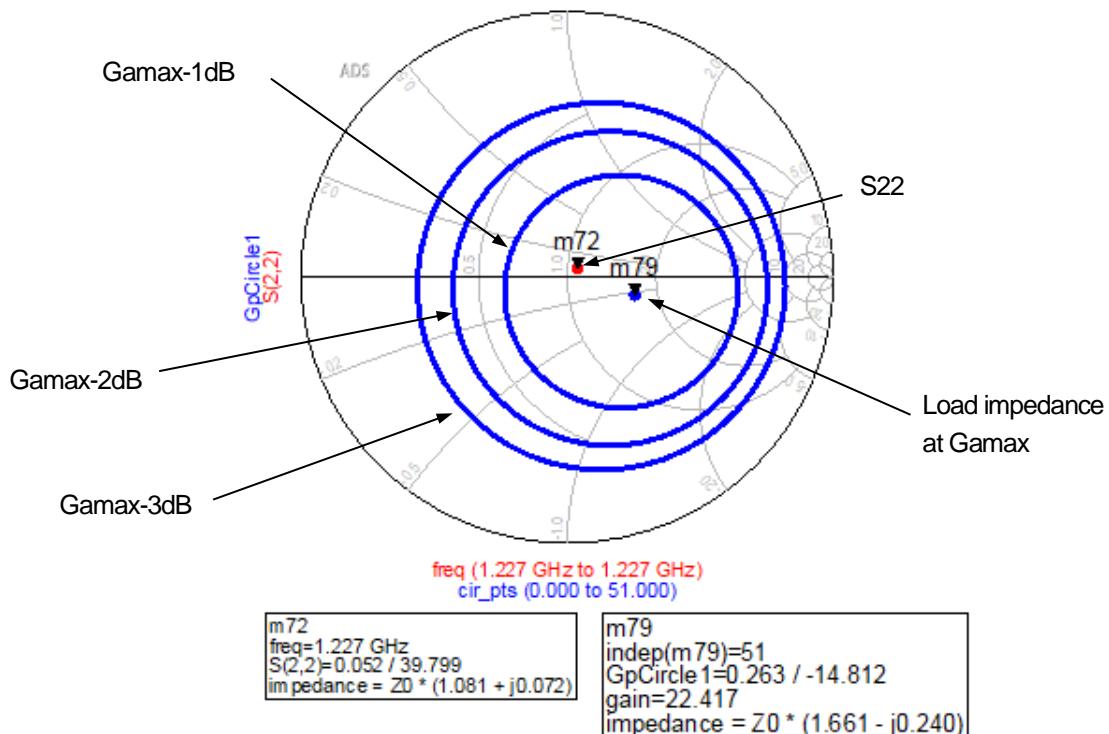


Condition: f=1.227GHz, V_{DD}=1.8V, V_{CTL}=1.8V, Ta=+25°C, Z_s=Z_l=50ohm

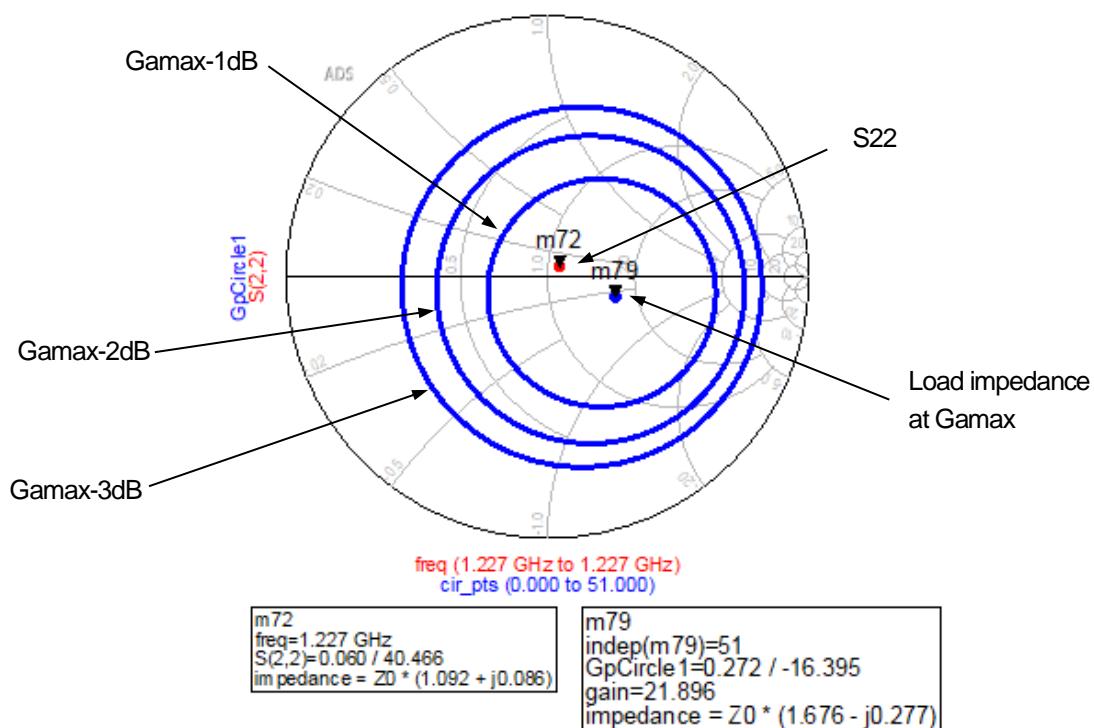


■ Gain circle simulation data (Load impedance)

Condition: $f=1.227\text{GHz}$, $V_{DD}=2.8\text{V}$, $V_{CTL}=1.8\text{V}$, $T_a=+25^\circ\text{C}$, $Z_s=Z_l=50\text{ohm}$

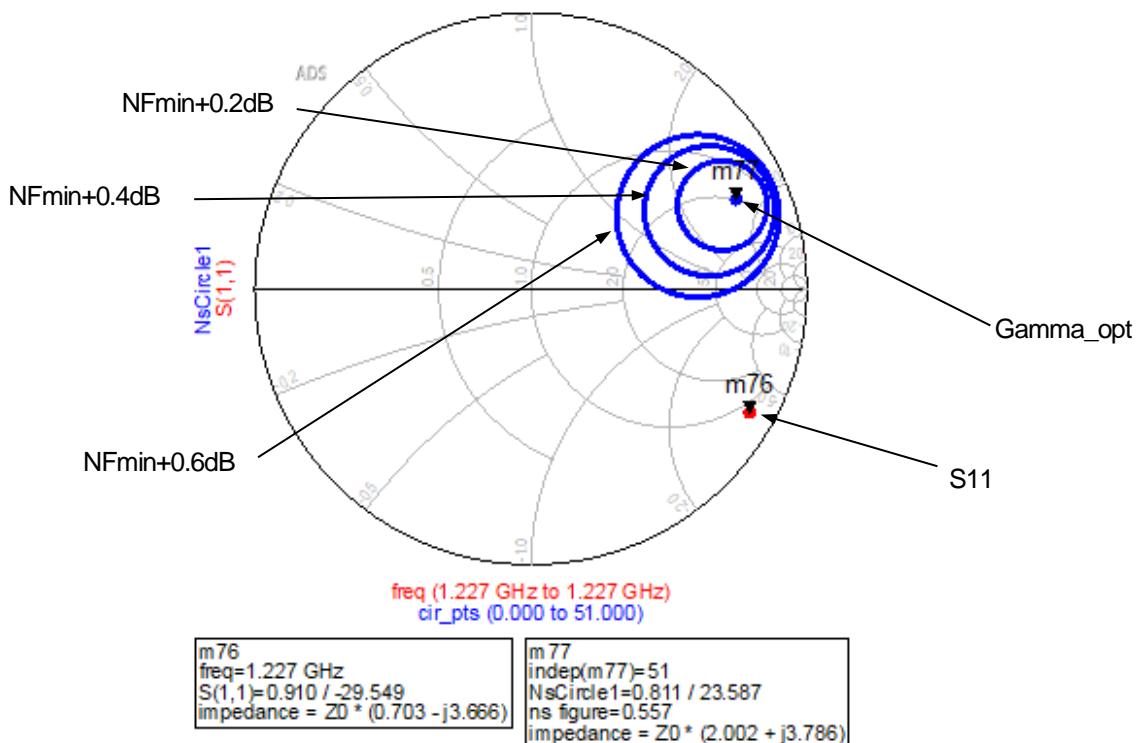


Condition: $f=1.227\text{GHz}$, $V_{DD}=1.8\text{V}$, $V_{CTL}=1.8\text{V}$, $T_a=+25^\circ\text{C}$, $Z_s=Z_l=50\text{ohm}$

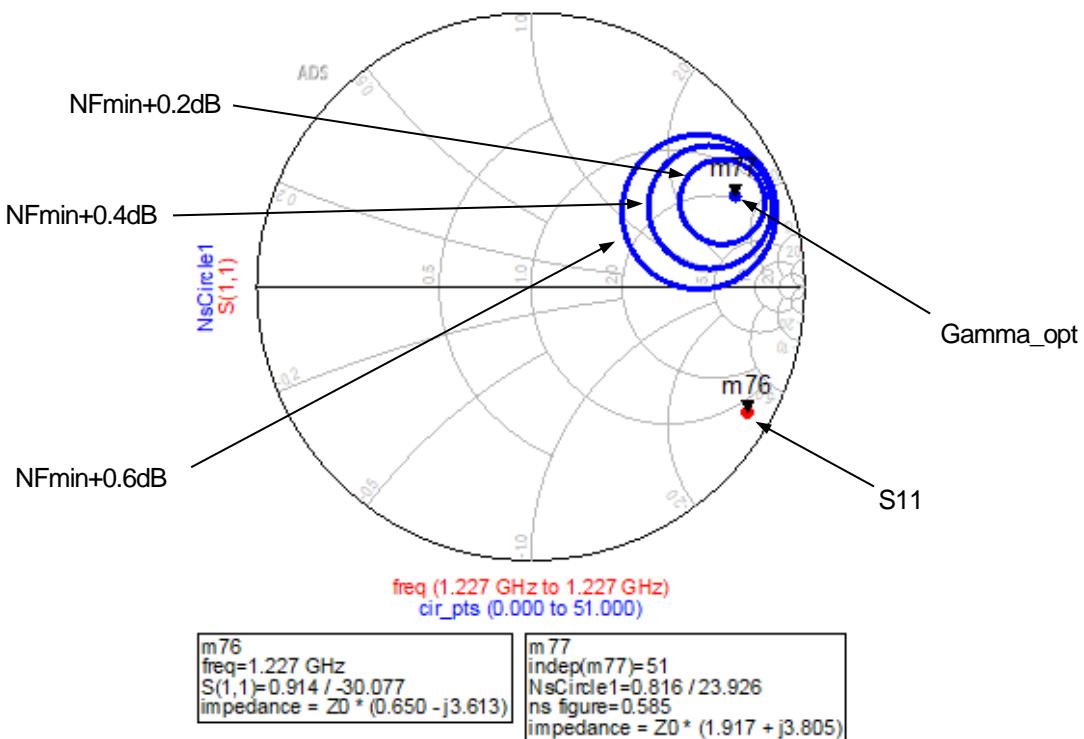


■ NF circle simulation data

Condition: f=1.227GHz, V_{DD}=2.8V, V_{CTL}=1.8V, Ta=+25°C, Z_s=Z_l=50ohm



Condition: f=1.227GHz, V_{DD}=1.8V, V_{CTL}=1.8V, Ta=+25°C, Z_s=Z_l=50ohm



■ Simulation condition

f = 50 MHz to 6GHz, Step = 5 MHz

T_a = +25 °C,

Z_s = Z_l = 50 ohm

s2p file at V_{DD}=2.8V : NT1192FAAE1S_2r8v_v0.s2p

s2p file at V_{DD}=1.8V : NT1192FAAE1S_1r8v_v0.s2p

■ Simulation circuit